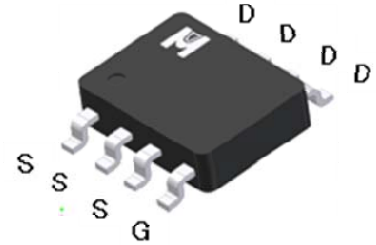


N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV <sub>DSS</sub>	60V
R <sub>DS(on)</sub> (MAX.)	55mΩ
I <sub>D</sub>	6A



UIS, R<sub>g</sub> 100% Tested

Pb-Free Lead Plating & Halogen Free



ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V <sub>GS</sub>	±20	V
Continuous Drain Current	T <sub>A</sub> = 25 °C	I <sub>D</sub>	6	A
	T <sub>A</sub> = 100 °C		4.5	
Pulsed Drain Current <sup>1</sup>		I <sub>DM</sub>	24	
Avalanche Current		I <sub>AS</sub>	6	
Avalanche Energy	L = 0.1mH, I <sub>D</sub> =6A, R <sub>G</sub> =25Ω	E <sub>AS</sub>	1.8	mJ
Repetitive Avalanche Energy <sup>2</sup>	L = 0.05mH	E <sub>AR</sub>	0.9	
Power Dissipation	T <sub>A</sub> = 25 °C	P <sub>D</sub>	2.5	W
	T <sub>A</sub> = 100 °C		1	
Operating Junction & Storage Temperature Range		T <sub>j</sub> , T <sub>stg</sub>	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	R <sub>θJC</sub>		25	°C / W
Junction-to-Ambient <sup>3</sup>	R <sub>θJA</sub>		50	

<sup>1</sup>Pulse width limited by maximum junction temperature.

<sup>2</sup>Duty cycle ≤ 1%

<sup>3</sup>50°C / W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper.

**ELECTRICAL CHARACTERISTICS (T<sub>c</sub> = 25 °C, Unless Otherwise Noted)**

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
<b>STATIC</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	60			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	1.0	2.0	3.2	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 48V, V <sub>GS</sub> = 0V			1	μA
		V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125 °C			25	
On-State Drain Current <sup>1</sup>	I <sub>D(ON)</sub>	V <sub>DS</sub> = 5V, V <sub>GS</sub> = 10V	6			A
Drain-Source On-State Resistance <sup>1</sup>	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 6A		45	55	mΩ
		V <sub>GS</sub> = 5V, I <sub>D</sub> = 5A		52	70	
Forward Transconductance <sup>1</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 6A		12		S
<b>DYNAMIC</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 30V, f = 1MHz		633		pF
Output Capacitance	C <sub>oss</sub>			67		
Reverse Transfer Capacitance	C <sub>rss</sub>			44		
Total Gate Charge <sup>1,2</sup>	Q <sub>g</sub>	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 6A		13.8		nC
Gate-Source Charge <sup>1,2</sup>	Q <sub>gs</sub>			2.8		
Gate-Drain Charge <sup>1,2</sup>	Q <sub>gd</sub>			4.0		
Turn-On Delay Time <sup>1,2</sup>	t <sub>d(on)</sub>	V <sub>DS</sub> = 30V, I <sub>D</sub> = 1A, V <sub>GS</sub> = 10V, R <sub>GS</sub> = 6Ω		10		nS
Rise Time <sup>1,2</sup>	t <sub>r</sub>			7.5		
Turn-Off Delay Time <sup>1,2</sup>	t <sub>d(off)</sub>			15		
Fall Time <sup>1,2</sup>	t <sub>f</sub>			10		
<b>SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T<sub>c</sub> = 25 °C)</b>						
Continuous Current	I <sub>S</sub>				2.3	A
Pulsed Current <sup>3</sup>	I <sub>SM</sub>				9.2	
Forward Voltage <sup>1</sup>	V <sub>SD</sub>	I <sub>F</sub> = I <sub>S</sub> , V <sub>GS</sub> = 0V			1.2	V

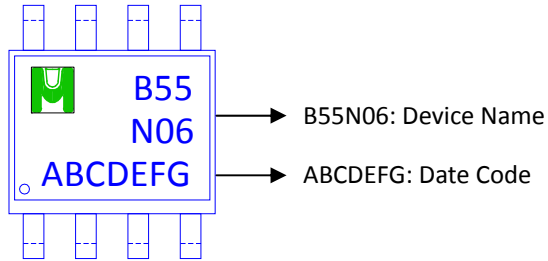
<sup>1</sup>Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

<sup>2</sup>Independent of operating temperature.

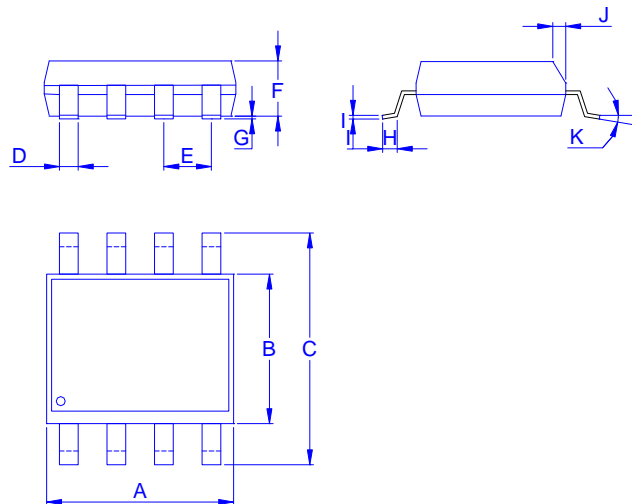
<sup>3</sup>Pulse width limited by maximum junction temperature.

Ordering & Marking Information:

Device Name: EMB55N06G for SOP-8



Outline Drawing



Dimension in mm

Dimension	A	B	C	D	E	F	G	H	I	J	K
Min.	4.70	3.70	5.80	0.33		1.20	0.08	0.40	0.19	0.25	0°
Typ.					1.27						
Max.	5.10	4.10	6.20	0.51		1.62	0.28	0.83	0.26	0.50	8°

